

VN0610LL

FET Transistor N-Channel — Enhancement



ON Semiconductor®

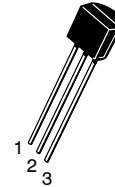
<http://onsemi.com>

MAXIMUM RATINGS

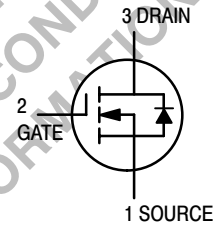
Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	Vdc
Drain-Gate Voltage ($R_{GS} = 1\text{ M}\Omega$)	V_{DGR}	60	Vdc
Gate-Source Voltage - Continuous - Non-repetitive ($t_p \leq 50\ \mu\text{s}$)	V_{GS} V_{GSM}	± 20 ± 40	Vdc Vpk
Drain Current Continuous Pulsed	I_D I_{DM}	190 1000	mAdc
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	400 3.2	mW mW/ $^\circ\text{C}$
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	312.5	$^\circ\text{C}/\text{W}$
Maximum Lead Temperature for Soldering Purposes, 1/16" from case for 10 seconds	T_L	300	$^\circ\text{C}$



CASE 29-11, STYLE 22
TO-92 (TO-226AA)



VN0610LL

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Drain-Source Breakdown Voltage (V _{GS} = 0, I _D = 100 μA)	V _{(BR)DSS}	60	—	Vdc
Zero Gate Voltage Drain Current (V _{DS} = 48 Vdc, V _{GS} = 0) (V _{DS} = 48 Vdc, V _{GS} = 0, T _J = 125°C)	I _{DSS}	—	10 500	μAdc
Gate-Body Leakage Current, Forward (V _{GSF} = 30 V, V _{DS} = 0)	I _{GSSF}	—	-100	nAdc

ON CHARACTERISTICS⁽¹⁾

Gate Threshold Voltage (V _{DS} = V _{GS} , I _D = 1.0 mA)	V _{GS(th)}	0.8	2.5	Vdc
Static Drain-Source On-Resistance (V _{GS} = 10 V, I _D = 500 mA) (V _{GS} = 10 V, I _D = 500 mA, T _C = 125°C)	r _{DS(on)}	—	5.0 9.0	Ω
Drain-Source On-Voltage (V _{GS} = 5.0 V, I _D = 200 mA) (V _{GS} = 10 V, I _D = 500 mA)	V _{DS(on)}	—	1.5 2.5	Vdc
On-State Drain Current (V _{GS} = 10 V, V _{DS} ≥ 2.0 V _{DS(on)})	I _{D(on)}	750	—	mAdc
Forward Transconductance (V _{DS} ≥ 2.0 V _{DS(on)} , I _D = 500 mA)	g _{fs}	100	—	μmhos

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

DYNAMIC CHARACTERISTICS

Input Capacitance	(V _{DS} = 25 Vdc, V _{GS} = 0, f = 1.0 MHz)	C _{iss}	—	60	pF
Output Capacitance		C _{oss}	—	25	
Reverse Transfer Capacitance		C _{rss}	—	5.0	

SWITCHING CHARACTERISTICS⁽¹⁾

Turn-On Delay Time	(V _{DD} = 15 Vdc, I _D = 600 mA, R _{gen} = 25 Ω, R _L = 23 Ω)	t _{on}	—	10	ns
Turn-Off Delay Time		t _{off}	—	10	

1. Pulse Test: Pulse Width ≤ 300 ms, Duty Cycle ≤ 10%.

RESISTIVE SWITCHING

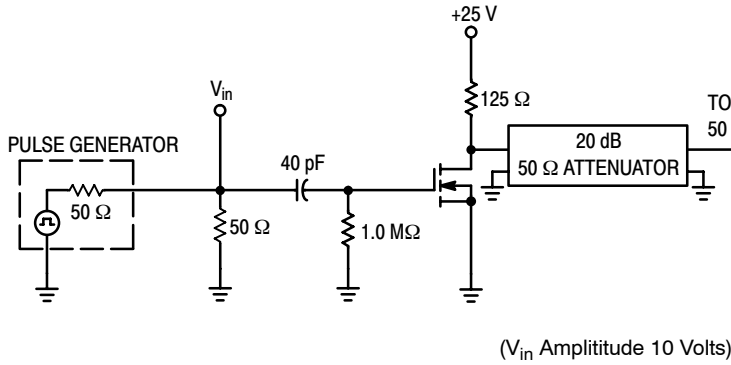


Figure 1. Switching Test Circuit

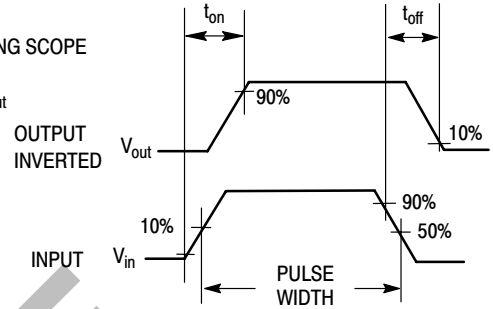


Figure 2. Switching Waveforms

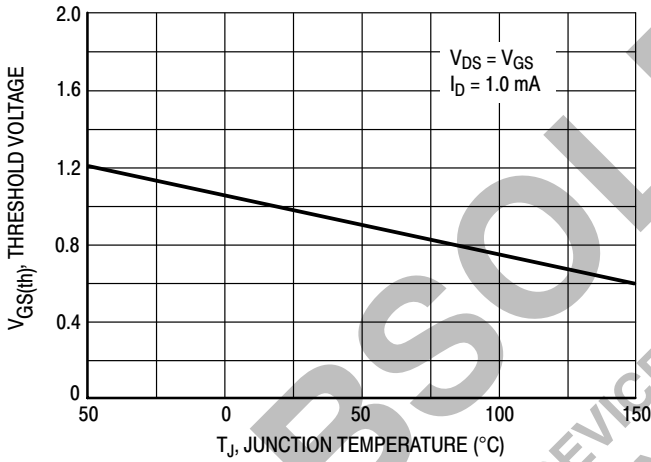


Figure 3. $V_{GS(th)}$ Normalized versus Temperature

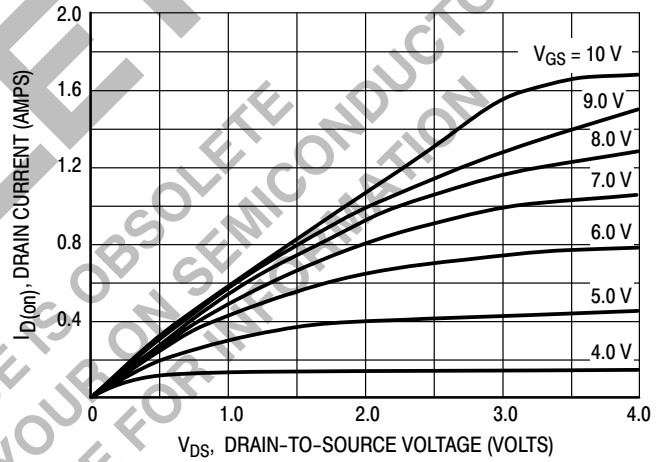


Figure 4. On-Region Characteristics

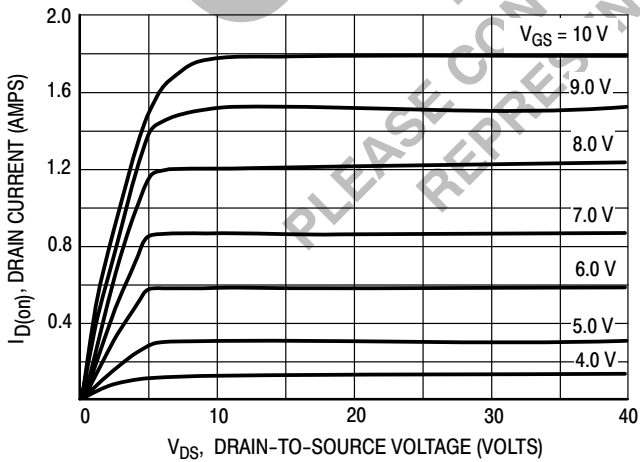


Figure 5. Output Characteristics

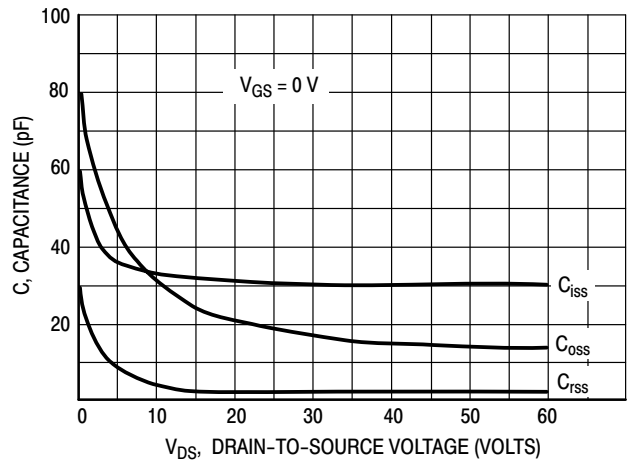
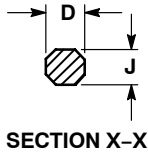
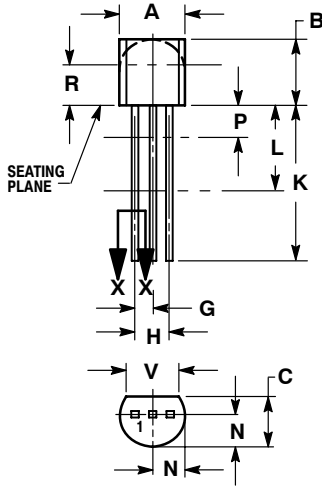


Figure 6. Capacitance versus Drain-To-Source Voltage

VN0610LL

PACKAGE DIMENSIONS

TO-92 (TO-226AA) CASE 29-11 ISSUE AL



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

STYLE 22:

1. SOURCE
2. GATE
3. DRAIN

ON Semiconductor and **ON** are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com
Order Literature: <http://www.onsemi.com/orderlit>
For additional information, please contact your local Sales Representative